

# ANTREX Electronics

## Electronic Components Sourcing Information

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### Product Reference Information

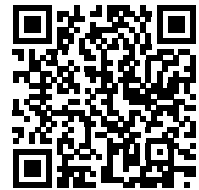
|                      |                           |
|----------------------|---------------------------|
| <b>Part Number:</b>  | DMTH6015LPDWQ-13          |
| <b>Manufacturer:</b> | Diodes Incorporated       |
| <b>Package:</b>      | Please confirm with sales |
| <b>Availability:</b> | Please confirm with sales |

#### Product Page:

<https://antrexco.com/product/details/diodes-incorporated/dmth6015lpdwq-13.html>

#### Request a Quote:

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### Contact Information

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### Quality & Trust

New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

#### Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

## Product Summary

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub>           | I <sub>D</sub><br>T <sub>C</sub> = +25°C |
|-------------------|-------------------------------|------------------------------------------|
| 60V               | 20mΩ @ V <sub>GS</sub> = 10V  | 36.3A                                    |
|                   | 27mΩ @ V <sub>GS</sub> = 4.5V | 31.2A                                    |

## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen- and Antimony-Free. "Green" Device (Note 3)**
- The DMTH6015LPDWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**  
<https://www.diodes.com/quality/product-definitions/>

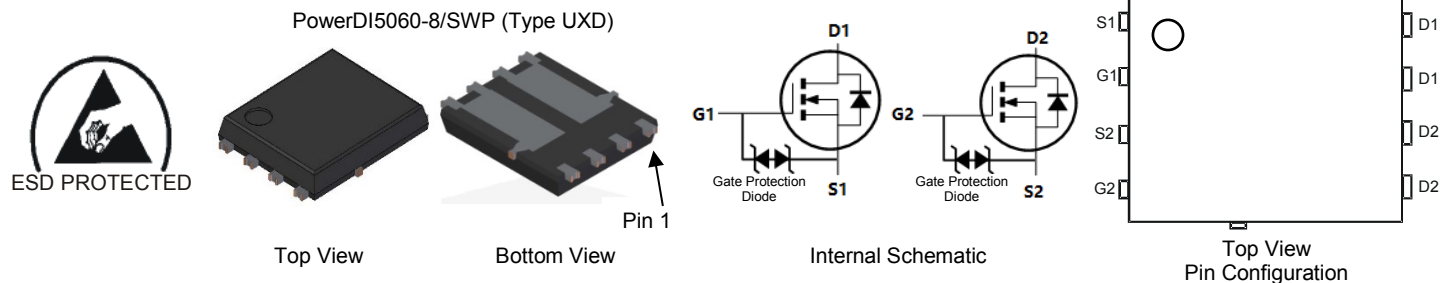
## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Wireless Charging
- DC-DC Converters
- Power Management

## Mechanical Data

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish – Matte Tin Annealed over Copper Lead-Frame; Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.097 grams (Approximate)

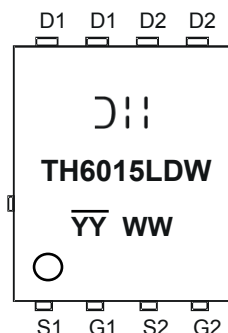


## Ordering Information (Note 4)

| Part Number      | Case                         | Packaging           |
|------------------|------------------------------|---------------------|
| DMTH6015LPDWQ-13 | PowerDI5060-8/SWP (Type UXD) | 2,500 / Tape & Reel |

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



Diodes logo = Manufacturer's Marking  
 TH6015LDW = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 20 = 2020)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                                                              |  |                                                                         | Symbol    | Value        | Unit |
|-----------------------------------------------------------------------------|--|-------------------------------------------------------------------------|-----------|--------------|------|
| Drain-Source Voltage                                                        |  |                                                                         | $V_{DSS}$ | 60           | V    |
| Gate-Source Voltage                                                         |  |                                                                         | $V_{GSS}$ | $\pm 16$     | V    |
| Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)                    |  | $T_C = +25^\circ\text{C}$<br>$T_C = +100^\circ\text{C}$                 | $I_D$     | 36.3<br>25.6 | A    |
| Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 5)                    |  | Steady State<br>$T_A = +25^\circ\text{C}$<br>$T_A = +100^\circ\text{C}$ | $I_D$     | 9.4<br>6.6   | A    |
| Pulsed Drain Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%)              |  |                                                                         | $I_{DM}$  | 140          | A    |
| Maximum Continuous Body Diode Forward Current (Note 5)                      |  |                                                                         | $I_S$     | 35           | A    |
| Pulsed Body Diode Forward Current (10 $\mu\text{s}$ Pulse, Duty Cycle = 1%) |  |                                                                         | $I_{SM}$  | 140          | A    |
| Avalanche Current $L = 0.1\text{mH}$                                        |  |                                                                         | $I_{AS}$  | 20.4         | A    |
| Avalanche Energy $L = 0.1\text{mH}$                                         |  |                                                                         | $E_{AS}$  | 20.8         | mJ   |

**Thermal Characteristics**

| Characteristic                                   |                           | Symbol          | Value       | Unit               |
|--------------------------------------------------|---------------------------|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 5)                 | $T_A = +25^\circ\text{C}$ | $P_D$           | 2.6         | W                  |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State              | $R_{\theta JA}$ | 57          | $^\circ\text{C/W}$ |
| Total Power Dissipation (Note 6)                 | $T_C = +25^\circ\text{C}$ | $P_D$           | 39.5        | W                  |
| Thermal Resistance, Junction to Case (Note 6)    |                           | $R_{\theta JC}$ | 3.8         | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range          |                           | $T_J, T_{STG}$  | -55 to +175 | $^\circ\text{C}$   |

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

| Characteristic                               | Symbol       | Min | Typ  | Max      | Unit          | Test Condition                                                              |
|----------------------------------------------|--------------|-----|------|----------|---------------|-----------------------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 7)</b>          |              |     |      |          |               |                                                                             |
| Drain-Source Breakdown Voltage               | $BV_{DSS}$   | 60  | —    | —        | V             | $V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$                                  |
| Zero Gate Voltage Drain Current              | $I_{DSS}$    | —   | —    | 1        | $\mu\text{A}$ | $V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$                                   |
| Gate-Source Leakage                          | $I_{GSS}$    | —   | —    | $\pm 10$ | $\mu\text{A}$ | $V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$                               |
| <b>ON CHARACTERISTICS (Note 7)</b>           |              |     |      |          |               |                                                                             |
| Gate Threshold Voltage                       | $V_{GS(TH)}$ | 1.3 | —    | 2.5      | V             | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$                                     |
| Static Drain-Source On-Resistance            | $R_{DS(ON)}$ | —   | 14.3 | 20       | m $\Omega$    | $V_{GS} = 10\text{V}, I_D = 10\text{A}$                                     |
|                                              |              | —   | 19.2 | 27       |               | $V_{GS} = 4.5\text{V}, I_D = 6\text{A}$                                     |
| Diode Forward Voltage                        | $V_{SD}$     | —   | 0.7  | 1.2      | V             | $V_{GS} = 0\text{V}, I_S = 1\text{A}$                                       |
| <b>DYNAMIC CHARACTERISTICS (Note 8)</b>      |              |     |      |          |               |                                                                             |
| Input Capacitance                            | $C_{iss}$    | —   | 825  | —        | pF            | $V_{DS} = 30\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$                  |
| Output Capacitance                           | $C_{oss}$    | —   | 244  | —        |               |                                                                             |
| Reverse Transfer Capacitance                 | $C_{rss}$    | —   | 20.5 | —        |               |                                                                             |
| Gate Resistance                              | $R_G$        | —   | 1.5  | —        | $\Omega$      | $V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$                   |
| Total Gate Charge ( $V_{GS} = 4.5\text{V}$ ) | $Q_g$        | —   | 7.1  | —        | nC            | $V_{DS} = 30\text{V}, I_D = 10\text{A}$                                     |
| Total Gate Charge ( $V_{GS} = 10\text{V}$ )  | $Q_g$        | —   | 14.3 | —        |               |                                                                             |
| Gate-Source Charge                           | $Q_{gs}$     | —   | 2.1  | —        |               |                                                                             |
| Gate-Drain Charge                            | $Q_{gd}$     | —   | 2.8  | —        |               |                                                                             |
| Turn-On Delay Time                           | $t_{D(ON)}$  | —   | 4.0  | —        | ns            | $V_{GS} = 10\text{V}, V_{DS} = 30\text{V}, R_G = 6\Omega, I_D = 10\text{A}$ |
| Turn-On Rise Time                            | $t_r$        | —   | 5.3  | —        |               |                                                                             |
| Turn-Off Delay Time                          | $t_{D(OFF)}$ | —   | 18.5 | —        |               |                                                                             |
| Turn-Off Fall Time                           | $t_f$        | —   | 8.0  | —        |               |                                                                             |
| Reverse Recovery Time                        | $t_{RR}$     | —   | 22.7 | —        | ns            | $I_F = 6\text{A}, di/dt = 100\text{A}/\mu\text{s}$                          |
| Reverse Recovery Charge                      | $Q_{RR}$     | —   | 12.8 | —        | nC            |                                                                             |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

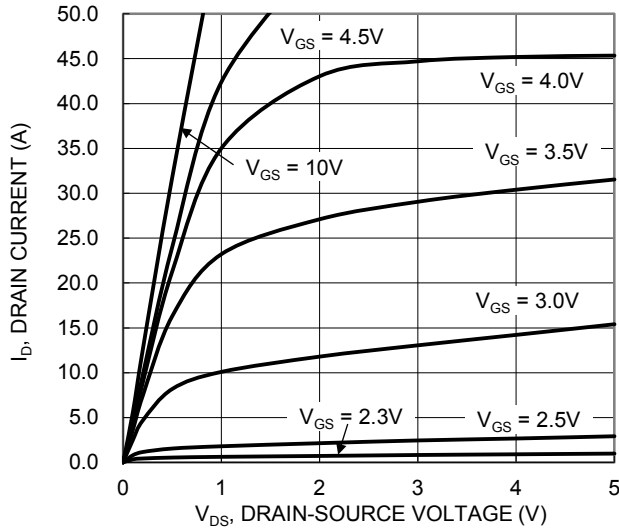


Figure 1. Typical Output Characteristic

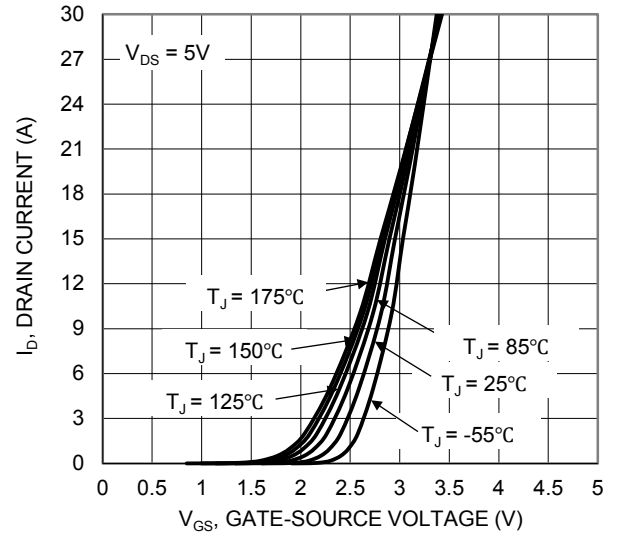


Figure 2. Typical Transfer Characteristic

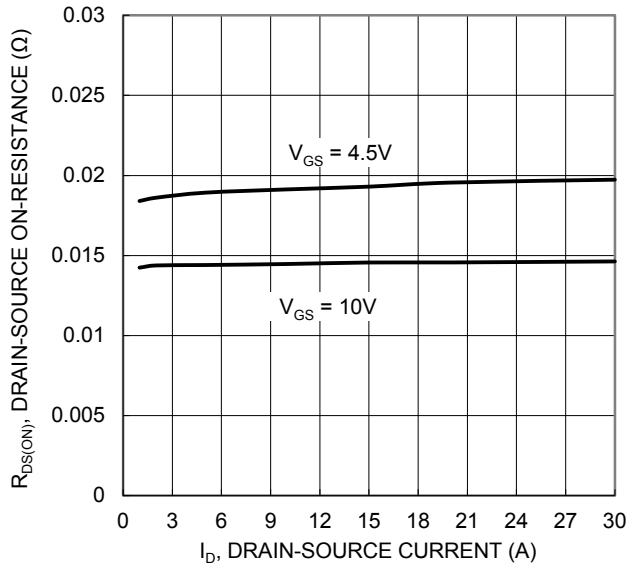


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

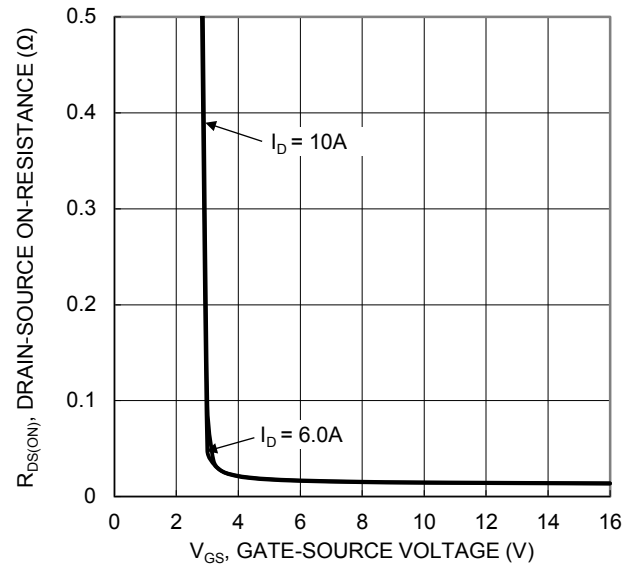


Figure 4. Typical Transfer Characteristic

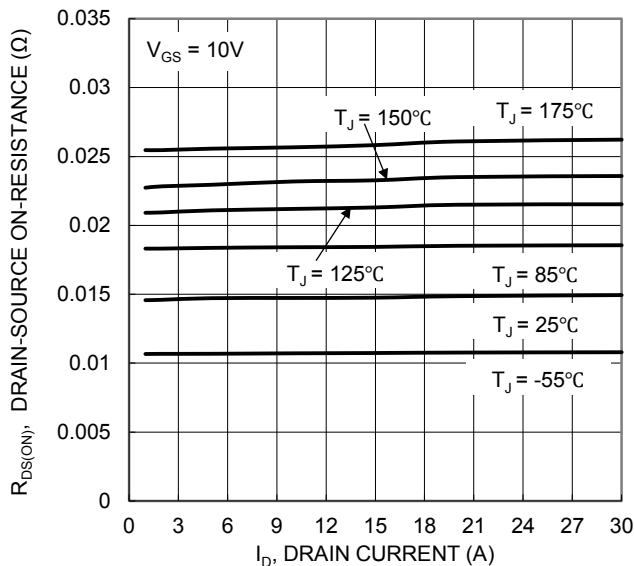


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

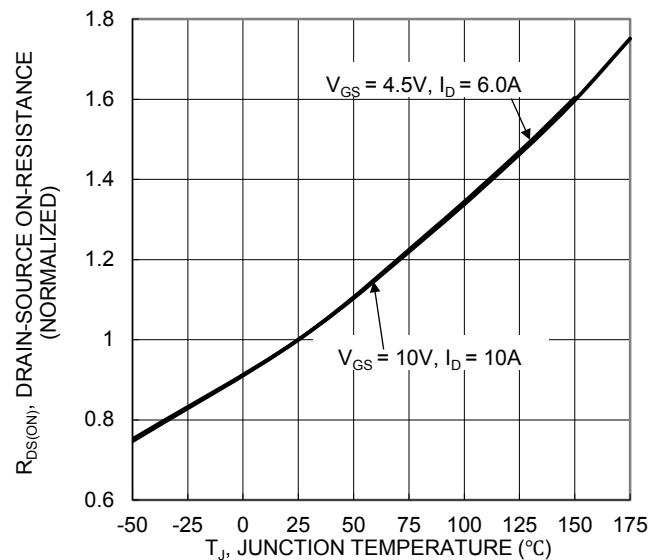


Figure 6. On-Resistance Variation with Junction Temperature

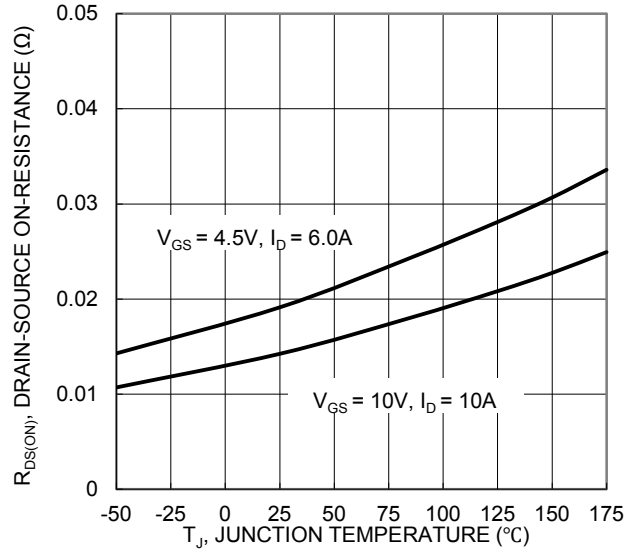


Figure 7. On-Resistance Variation with Junction Temperature

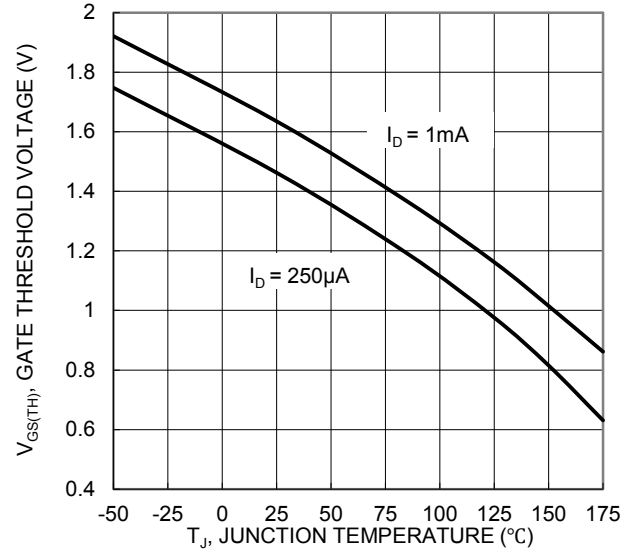


Figure 8. Gate Threshold Variation vs. Junction Temperature

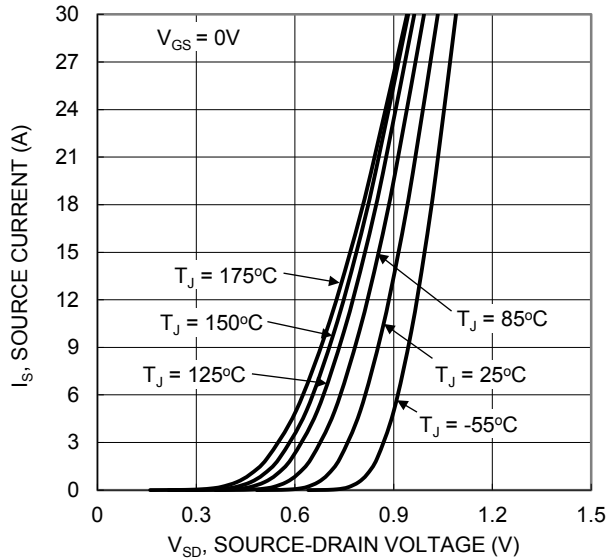


Figure 9. Diode Forward Voltage vs. Current

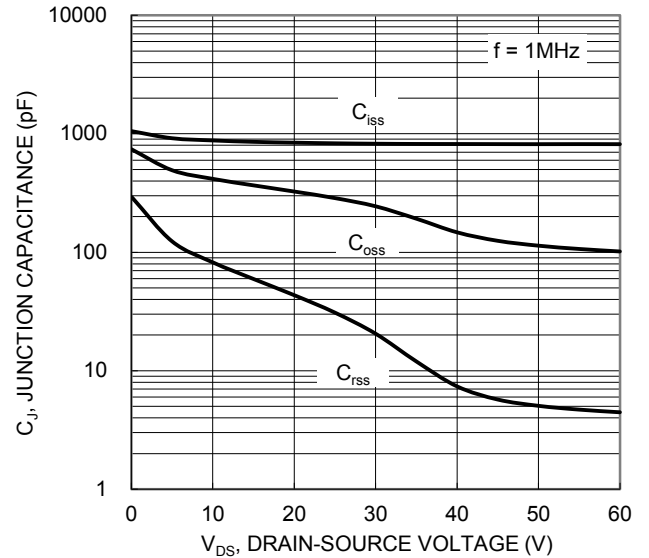


Figure 10. Typical Junction Capacitance

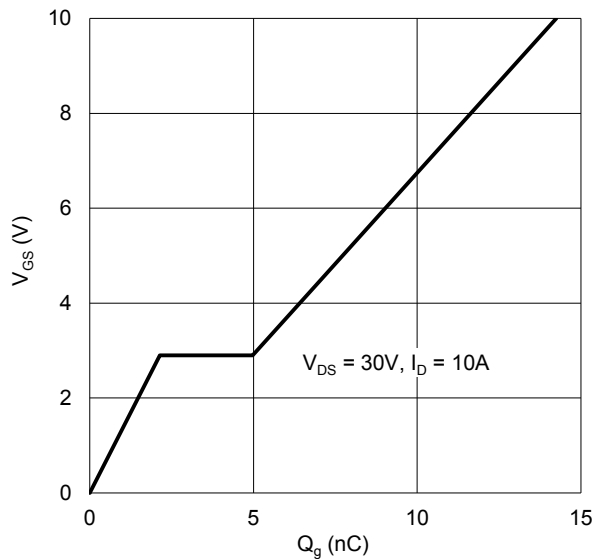


Figure 11. Gate Charge

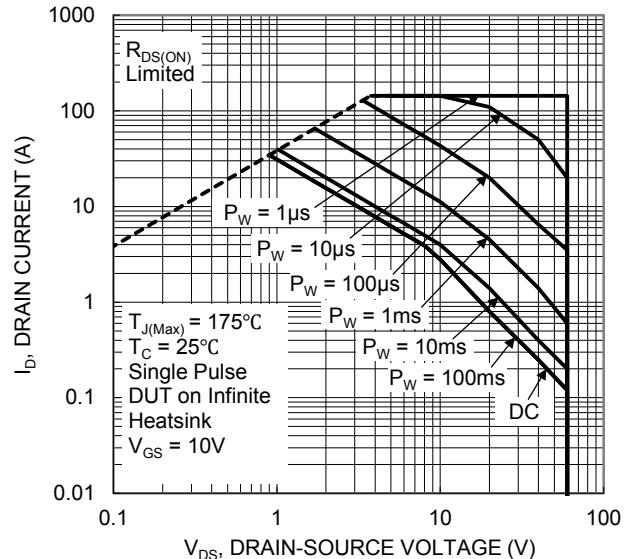


Figure 12. SOA, Safe Operation Area

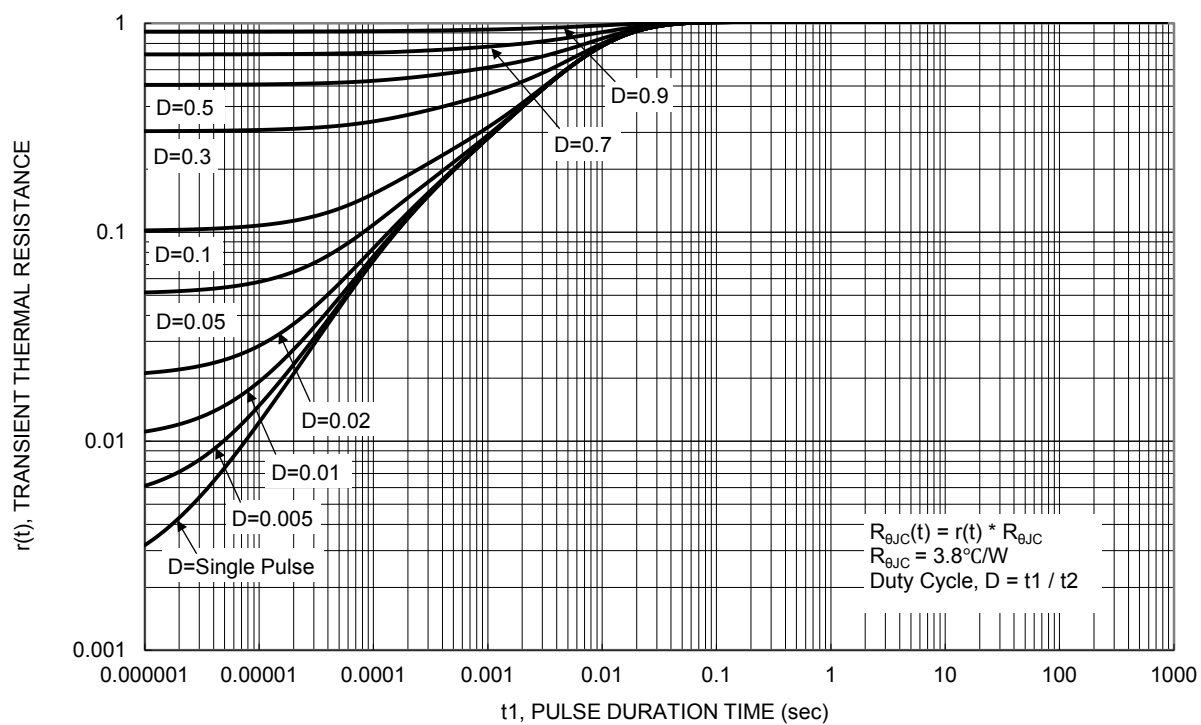
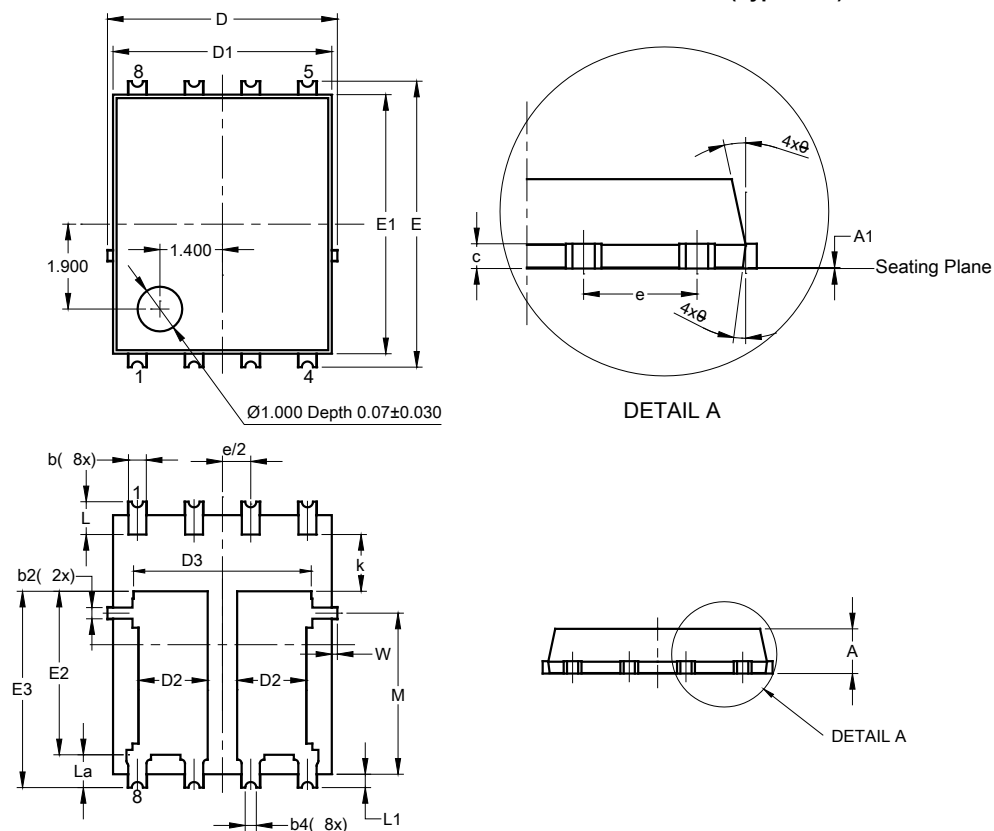


Figure 13. Transient Thermal Resistance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8/SWP (Type UXD)**

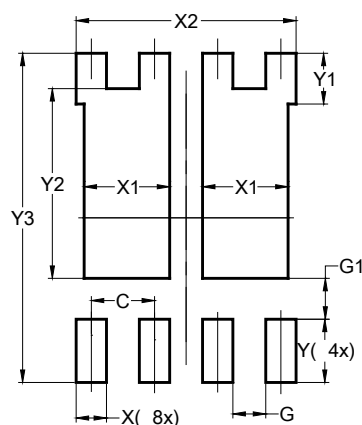


| PowerDI5060-8/SWP<br>(Type UXD) |          |       |       |
|---------------------------------|----------|-------|-------|
| Dim                             | Min      | Max   | Typ   |
| A                               | 0.90     | 1.10  | 1.00  |
| A1                              | 0.00     | 0.05  | --    |
| b                               | 0.30     | 0.50  | 0.41  |
| b2                              | 0.20     | 0.35  | 0.25  |
| b4                              | 0.25REF  |       |       |
| c                               | 0.230    | 0.330 | 0.277 |
| D                               | 5.15 BSC |       |       |
| D1                              | 4.70     | 5.10  | 4.90  |
| D2                              | 1.46     | 1.66  | 1.55  |
| D3                              | 3.78     | 4.18  | 3.98  |
| E                               | 6.40 BSC |       |       |
| E1                              | 5.60     | 6.00  | 5.80  |
| E2                              | 3.46     | 3.86  | 3.66  |
| E2a                             | 4.195    | 4.595 | 4.395 |
| e                               | 1.27BSC  |       |       |
| k                               | 1.05     | --    | --    |
| L                               | 0.635    | 0.835 | 0.735 |
| La                              | 0.635    | 0.835 | 0.735 |
| L1                              | 0.200    | 0.400 | 0.300 |
| M                               | 3.205    | 4.005 | 3.605 |
| W                               | 0.025    | 0.225 | 0.125 |
| θ                               | 10°      | 12°   | 11°   |
| θ1                              | 6°       | 8°    | 7°    |
| All Dimensions in mm            |          |       |       |

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI5060-8/SWP (Type UXD)**



| Dimensions | Value<br>(in mm) |
|------------|------------------|
| C          | 1.270            |
| G          | 0.660            |
| G1         | 0.820            |
| X          | 0.610            |
| X1         | 1.720            |
| X2         | 4.420            |
| Y          | 1.270            |
| Y1         | 1.020            |
| Y2         | 3.810            |
| Y3         | 6.610            |

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